

# NTHS4501N

## Power MOSFET

### 30 V, 6.7 A, Single N-Channel, ChipFET™ Package

#### Features

- Planar Technology Device Offers Low  $R_{DS(on)}$  and Fast Switching Speed in a ChipFET Package
- Leadless ChipFET Package has 40% Smaller Footprint than TSOP-6. Ideal Device for Applications Where Board Space is at a Premium.
- ChipFET Package Exhibits Excellent Thermal Capabilities Where Heat Transfer is Required.
- Pb-Free Package is Available

#### Applications

- Buck and Boost Converters
- Optimized for Battery and Load Management Applications in Portable Equipment such as Notebook Computers, MP3 Players, Cell Phones, Digital Cameras, Personal Digital Assistants and Other Portable Applications
- Charge Control in Battery Chargers

#### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit	
Drain-to-Source Voltage		$V_{DSS}$	30	V	
Gate-to-Source Voltage		$V_{GS}$	$\pm 20$	V	
Continuous Drain Current (Note 1)	Steady State	$I_D$	$T_A = 25^\circ\text{C}$	4.9	A
			$T_A = 85^\circ\text{C}$	3.5	
	$t \leq 5$ s	$T_A = 25^\circ\text{C}$	6.7		
Power Dissipation (Note 1)	Steady State	$P_D$	$T_A = 25^\circ\text{C}$	1.3	W
			$T_A = 85^\circ\text{C}$	0.7	
	$t \leq 5$ s	$T_A = 25^\circ\text{C}$	2.5		
Pulsed Drain Current	$t_p = 10$ $\mu\text{s}$	$I_{DM}$	20	A	
Operating Junction and Storage Temperature		$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$	
Source Current (Body Diode)		$I_S$	1.1	A	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		$T_L$	260	$^\circ\text{C}$	

#### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient – Steady State (Note 1)	$R_{\theta JA}$	95	$^\circ\text{C}/\text{W}$
Junction-to-Foot (Drain) Steady State (Note 1)	$R_{\theta JF}$	20	
Junction-to-Ambient – $t \leq 5$ s (Note 1)	$R_{\theta JA}$	50	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

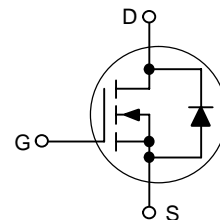
1. Surface Mounted on FR4 Board using 1 in sq. pad size (Cu area = 1.127 in sq [1 oz] including traces).



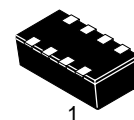
ON Semiconductor®

<http://onsemi.com>

$V_{(BR)DSS}$	$R_{DS(on)}$ Typ	$I_D$ Max
30 V	30 m $\Omega$ @ 10 V	6.7 A
	40 m $\Omega$ @ 4.5 V	

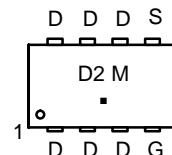


N-Channel MOSFET



ChipFET  
CASE 1206A  
STYLE 1

#### MARKING DIAGRAM AND PIN ASSIGNMENT



- D2 = Specific Device Code
- M = Month Code
- = Pb-Free Package

#### ORDERING INFORMATION

Device	Package	Shipping†
NTHS4501NT1	ChipFET	3000/Tape & Reel
NTHS4501NT1G	ChipFET (Pb-Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

# NTHS4501N

## ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
<b>OFF CHARACTERISTICS</b>						
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	30	31		V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V <sub>(BR)DSS</sub> /T <sub>J</sub>			30		mV/°C
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 24 V	T <sub>J</sub> = 25°C		1.0	μA
			T <sub>J</sub> = 125°C		10	
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±20 V			100	nA

## ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 250 μA	1.0	1.6	2.0	V
Negative Threshold Temperature Coefficient	V <sub>GS(TH)</sub> /T <sub>J</sub>			4.0		mV/°C
Drain-to-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 4.9 A		30	38	mΩ
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 3.9 A		40	50	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 4.9 A		15		S

## CHARGES AND CAPACITANCES

Input Capacitance	C <sub>ISS</sub>	V <sub>GS</sub> = 0 V, f = 1.0 MHz, V <sub>DS</sub> = 24 V		462		pF
Output Capacitance	C <sub>OSS</sub>			137		
Reverse Transfer Capacitance	C <sub>RSS</sub>			32		
Total Gate Charge	Q <sub>G(TOT)</sub>	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 15 V, I <sub>D</sub> = 4.9 A		9.1		nC
Threshold Gate Charge	Q <sub>G(TH)</sub>			0.7		
Gate-to-Source Charge	Q <sub>GS</sub>			1.3		
Gate-to-Drain Charge	Q <sub>GD</sub>			1.8		

## SWITCHING CHARACTERISTICS (Note 3)

Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 15 V, I <sub>D</sub> = 1.0 A, R <sub>G</sub> = 6.0 Ω		4.0		ns
Rise Time	t <sub>r</sub>			11		
Turn-Off Delay Time	t <sub>d(off)</sub>			17		
Fall Time	t <sub>f</sub>			7.5		

## DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V <sub>SD</sub>	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 1.1 A	T <sub>J</sub> = 25°C	0.75	1.2	V
Reverse Recovery Time	t <sub>RR</sub>	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 1.1 A, dI <sub>S</sub> /dt = 90 A/μs		19.1		ns
Charge Time	t <sub>a</sub>			11.9		
Discharge Time	t <sub>b</sub>			7.3		
Reverse Recovery Charge	Q <sub>RR</sub>			13		nC

2. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

3. Switching characteristics are independent of operating junction temperatures.

TYPICAL PERFORMANCE CURVES ( $T_J = 25^\circ\text{C}$  unless otherwise noted)

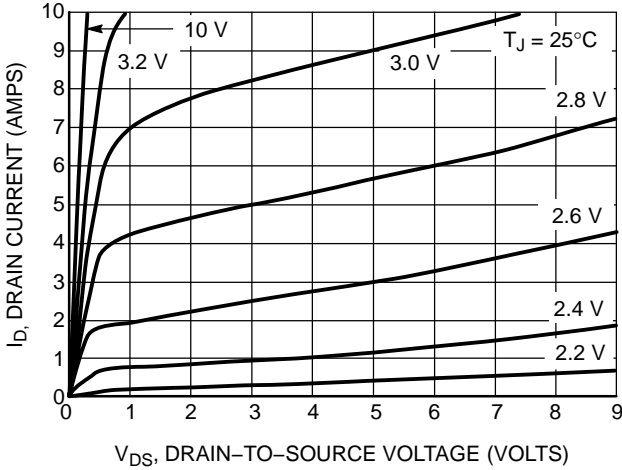


Figure 1. On-Region Characteristics

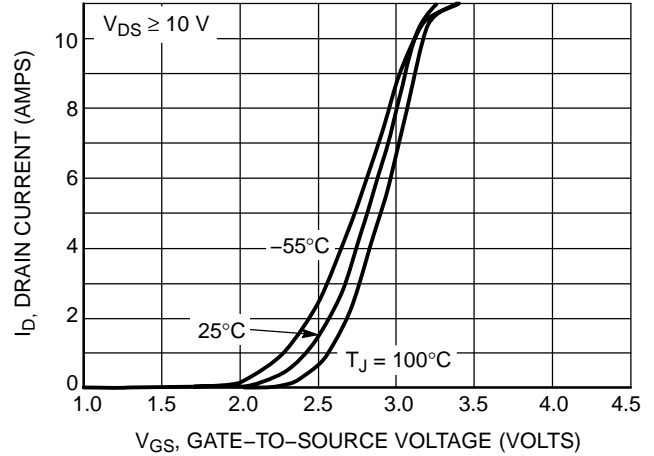


Figure 2. Transfer Characteristics

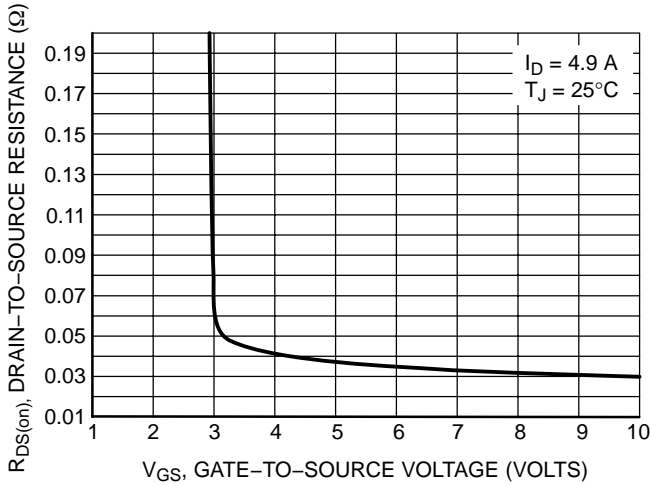


Figure 3. On-Resistance vs. Gate-to-Source Voltage

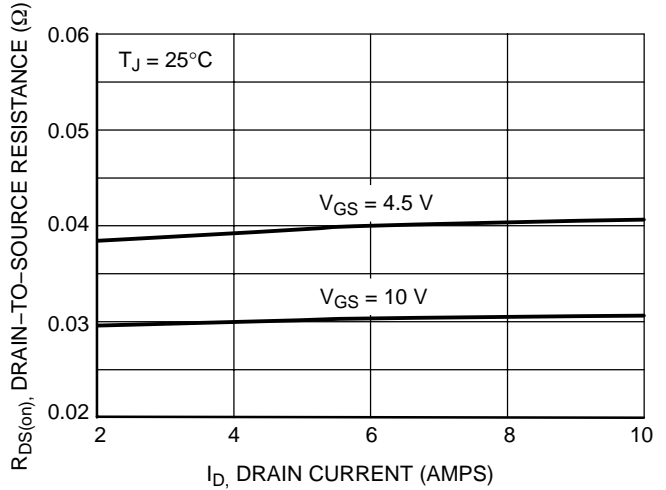


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

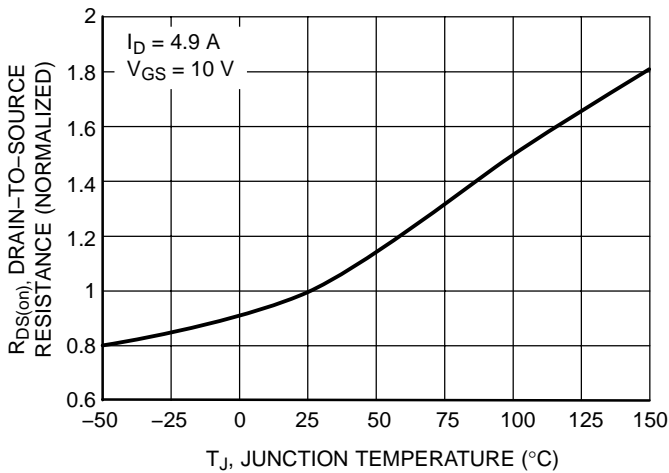


Figure 5. On-Resistance Variation with Temperature

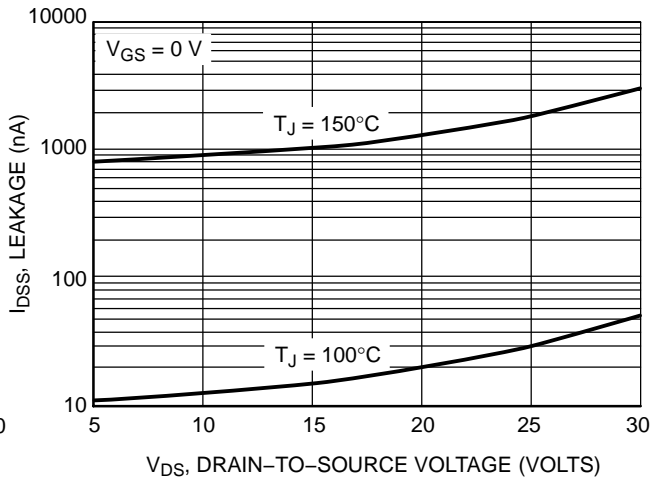


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL PERFORMANCE CURVES ( $T_J = 25^\circ\text{C}$  unless otherwise noted)

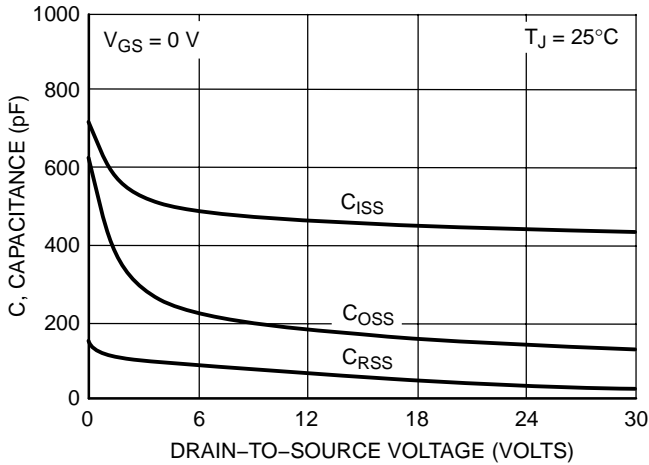


Figure 7. Capacitance Variation

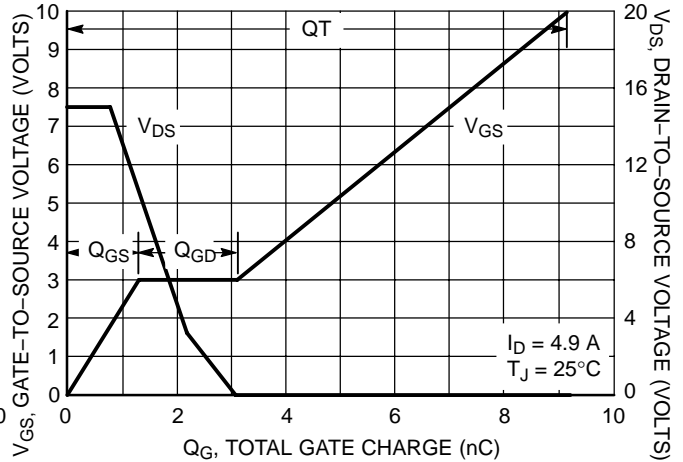


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

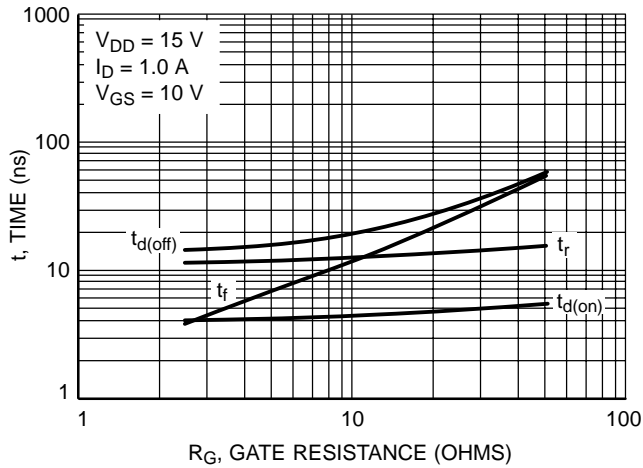


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

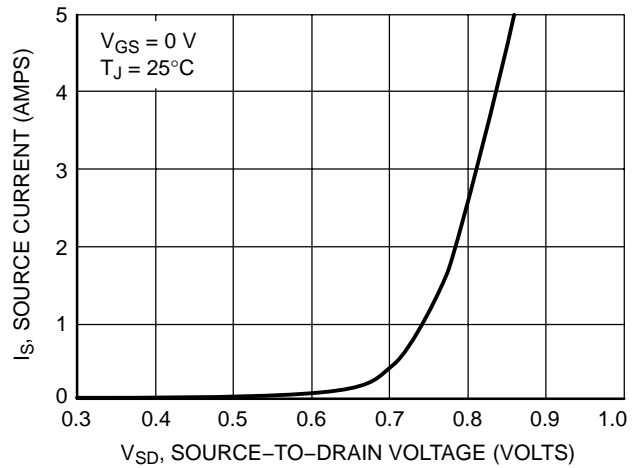
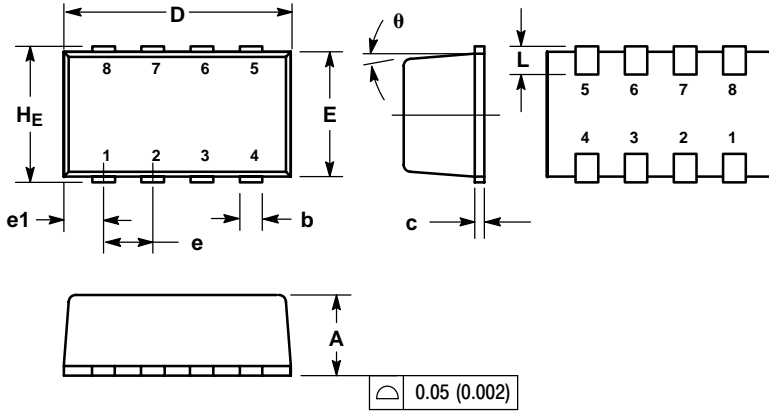


Figure 10. Diode Forward Voltage vs. Current

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## PACKAGE DIMENSIONS

ChipFET™  
CASE 1206A-03  
ISSUE H



### NOTES:

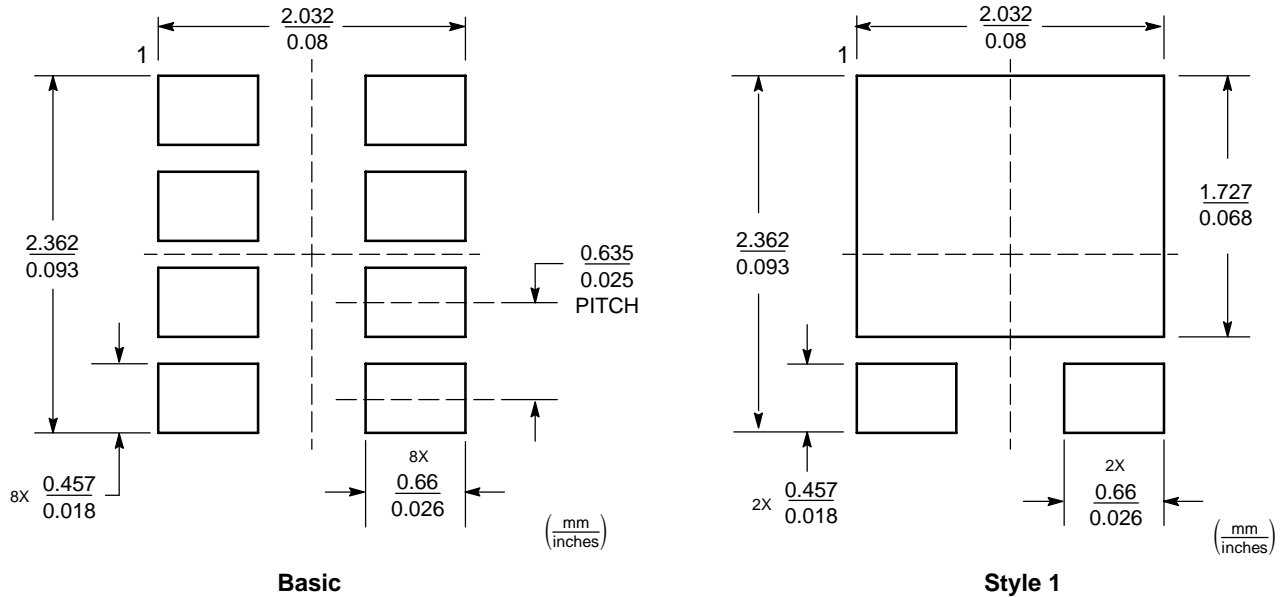
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. MOLD GATE BURRS SHALL NOT EXCEED 0.13 MM PER SIDE.
4. LEADFRAME TO MOLDED BODY OFFSET IN HORIZONTAL AND VERTICAL SHALL NOT EXCEED 0.08 MM.
5. DIMENSIONS A AND B EXCLUSIVE OF MOLD GATE BURRS.
6. NO MOLD FLASH ALLOWED ON THE TOP AND BOTTOM LEAD SURFACE.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.00	1.05	1.10	0.039	0.041	0.043
b	0.25	0.30	0.35	0.010	0.012	0.014
c	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
E	1.55	1.65	1.70	0.061	0.065	0.067
e	0.65 BSC			0.025 BSC		
e1	0.55 BSC			0.022 BSC		
L	0.28	0.35	0.42	0.011	0.014	0.017
HE	1.80	1.90	2.00	0.071	0.075	0.079
θ	5° NOM			5° NOM		

### STYLE 1:

- PIN 1. DRAIN
- 2. DRAIN
- 3. DRAIN
- 4. GATE
- 5. SOURCE
- 6. DRAIN
- 7. DRAIN
- 8. DRAIN


## SOLDERING FOOTPRINTS\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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